TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2 S C 5 2 4 2

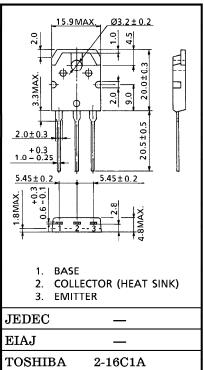
POWER AMPLIFIER APPLICATIONS

- High Collector Breakdown Voltage: VCEO=230V (Min.)
- Complementary to 2SA1962
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	230	V
Collector-Emitter Voltage	V_{CEO}	230	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	IC	15	A
Base Current	$I_{\mathbf{B}}$	1.5	A
Collector Power Dissipation (Tc=25°C)	PC	130	W
Junction Temperature	Tj	150	°C
Storage Temperature	$T_{ m stg}$	-55~150	°C

Unit in mm



Weight: 4.7g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Collector Output Capacitance

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 230V, I_{E} = 0$	_	_	5.0	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_{C}=0$	_	_	5.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C}$ =50mA, $I_{\rm B}$ =0	230	_		V
DC Current Gain (N	hFE (1) (Note)	$V_{\rm CE}$ =5V, $I_{\rm C}$ =1A	55	_	160	
	h _{FE (2)}	$V_{CE}=5V, I_{C}=7A$	35	60	—	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	$I_{C}=8A, I_{B}=0.8A$	_	0.4	3.0	V
Base-Emitter Voltage	$v_{ m BE}$	$V_{CE}=5V, I_{C}=7A$	_	1.0	1.5	V
Transition Frequency	fr	$V_{CE} = 5V$, $I_{C} = 1A$		30		MHz

 $V_{CB} = 10V, I_E = 0, f = 1MHz$

Note: hFE(1) Classification $R:55\sim110, O:80\sim160$

 C_{ob}

рF

200

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